

## Defect Engineering of SrTiO<sub>3</sub> thin films for resistive switching applications

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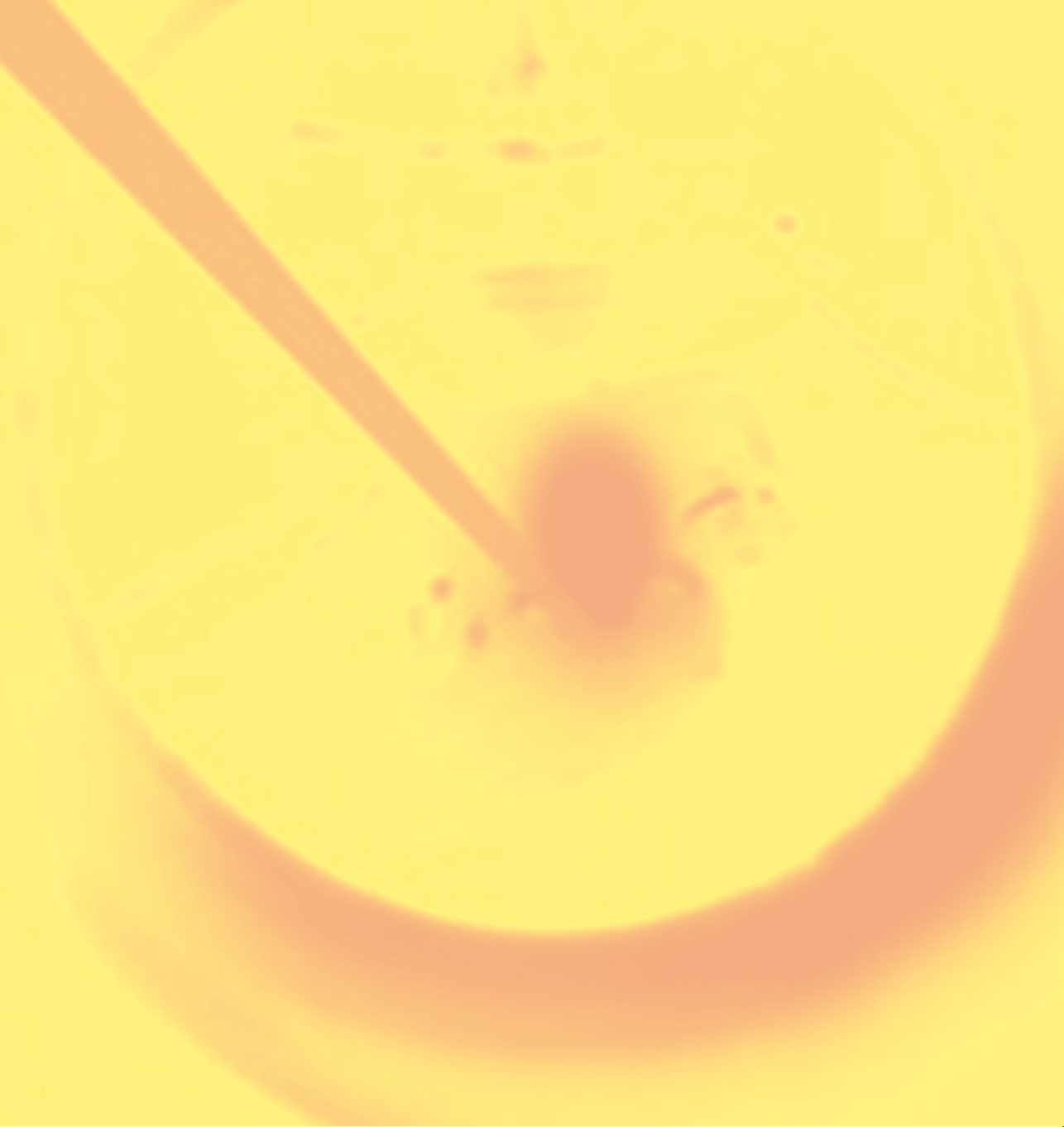
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